
#### Abstract

This report presents the effect of neutron displacement damage (NDD) on the TPS7H3301-SP device. The results show that all devices were fully functional and within production test limits after having been irradiated up to a neutron fluence of $1 \times 10^{13} \mathrm{n} / \mathrm{cm}^{2}$ ( $1-\mathrm{MeV}$ equivalent). A sample size of nine units was exposed to radiation testing per (MIL-STD-883, Method 1017 for Neutron Irradiation) and an additional unirradiated sample device was used for correlation. All devices used in the experiment were from lot date code 1729A and assembly lot 7003811 . Electrical testing was performed at Texas Instruments before and after neutron irradiation using the production test program for TPS7H3301-SP.


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## 1 Overview

The TPS7H3301-SP is a radiation-hardened double data rate (DDR) 3-A termination regulator with built-in VTTREF buffer. The regulator is specifically design to provide a complete, compact, low-noise solution for space DDR termination applications such as single board computers, solid state recorders, and payload processing.

General device information and testing conditions are listed in Table 1.
Table 1. Overview Information

| TI Part Number | TPS7H3301-SP |
| :---: | :---: |
| SMD Number | 5962R1422801VXC |
| Device Function | DDR 3-A Termination Regulator |
| Die Name | RTPS7H3301A1VM |
| Technology | LBC7 |
| A/T Lot Number / Date Code | $7003811 / 1729 \mathrm{~A}$ |
| Unbiased Quantity Tested | 9 |
| Exposure Facility | VPT Rad |
| Neutron Fluence (1-MeV equivalent) | $1.0 \times 10^{12}, 5.0 \times 10^{12}, 1.0 \times 10^{13} \mathrm{n} / \mathrm{cm}^{2}$ |
| Irradiation Temperature | $25^{\circ} \mathrm{C}$ |

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## 2 Test Procedures

The TPS7H3301-SP was electrically pre-tested using the production automated test equipment program. General test procedures were MIL-STD-883, Method 1017 for Neutron Irradiation of TPS7H3301-SP.

Table 2. Neutron Irradiation Conditions

| Group | Sample Qty | Neutron Fluence (n/cm $\left.{ }^{\mathbf{2}}\right)$ | Bias |
| :---: | :---: | :---: | :---: |
| A | 3 | $1.0 \times 10^{12}$ | Unbiased |
| B | 3 | $5.0 \times 10^{12}$ | Unbiased |
| C | 3 | $1.0 \times 10^{13}$ | Unbiased |



Figure 1. TPS7H3301-SP Device

## 3 Facility

The University of Massachusetts's Fast Neutron Irradiation (FNI) facility is an experimental facility that replaced the three beam ports that originally existed on the left side of the research reactor. It is designed to give a fast flux level $\geq 1011 \mathrm{n} / \mathrm{cm}^{2}-\mathrm{s}$, with relatively low thermal fluence and gamma dose rates.
Samples with a cross-sectional area as large as $30 \mathrm{~cm}(12 \mathrm{in}) \times 30 \mathrm{~cm}(12 \mathrm{in})$ and up to 15 cm (6 in) thick can be irradiated. The fast neutron flux is designed to be nearly uniform over the $30-\mathrm{cm}$ ( $12-\mathrm{in}$ ) $\times 30-\mathrm{cm}$ ( $12-\mathrm{in}$ ) area facing the core, and the fast fluence variation through the sample thickness is minimized via a single $180^{\circ}$ rotation of the sample canister at the midpoint of the irradiation period. The FNI facility offers a significantly larger sample volume than previously available within the University of Massachusetts Lowell Research Reactor (UMLRR).
The fluences are calculated based on 1-MeV equivalences.
Detailed information of the radiation facility is available at the following link:
www.uml.edu/docs/FNI\ Brochure_tcm18-90375.pdf

## 4 Results

There were no functional failures at any irradiation level. All parametric measurements remained well within all data sheet (SLVSCJ5) limits for all exposure levels. All parametric measurements remained well within the production test limits which are guard-banded from the data sheet limits.
The full parameter list and graphs are found in Appendix A
Table 3 lists the TPS7H3301-SP specification compliance matrix.
Table 3. TPS7H3301-SP Specifications

| PARAMETER |  | TEST CONDITION | TPS7H3301-SP |  |  |  | ATE Test \# |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | MIN | TYP | MAX | UNIT |  |
| $\mathrm{V}_{\mathrm{O}} / \mathrm{V}_{\text {TT }}$ OUTPUT |  |  |  |  |  |  |  |
| $\mathrm{V}_{\text {LDOIN }}-\mathrm{V}_{\text {TT }}$ | $\mathrm{V}_{\text {LDOIN }}>\mathrm{V}_{\text {TT }}$ |  | $\begin{aligned} & \mathrm{VIN} / \mathrm{VDD}=2.95 \mathrm{~V}, \mathrm{VVDDQSNS}=2.5 \mathrm{~V}, \mathrm{VTT}=\mathrm{VVTTREF}-50 \mathrm{mV} \text { (DDR1), } \\ & \mathrm{IO}=0.5 \mathrm{~A} \end{aligned}$ |  | 62 | 230 | mV | 26.x |
|  |  | $\begin{aligned} & \text { VIN / VDD=2.95 V, VVDDQSNS=2.5V, VTT=VVTTREF - 50mV (DDR1), } \\ & \text { IO=1A } \end{aligned}$ |  | 129 | 300 | mV | 26.x |
|  |  | $\begin{aligned} & \text { VIN / VDD=2.95 V, VVDDQSNS=2.5V, VTT=VVTTREF - } 50 \mathrm{mV} \text { (DDR1), } \\ & \mathrm{IO}=2 \mathrm{~A} \end{aligned}$ |  | 272 | 400 | mV | 26.x |
|  |  | $\begin{aligned} & \mathrm{VIN} / \mathrm{VDD}=2.375 \mathrm{~V}, \mathrm{VVDDQSNS}=1.8 \mathrm{~V}, \mathrm{VTT}=\mathrm{VVTTREF}-50 \mathrm{mV} \text { (DDR2), } \\ & \mathrm{IO}=0.5 \mathrm{~A} \end{aligned}$ |  | 57 | 230 | mV | 27.x |
|  |  | VIN / VDD=2.375V, VVDDQSNS=1.8V, VTT=VVTTREF - 50mV (DDR2), $10=1 \mathrm{~A}$ |  | 118 | 300 | mV | 27.x |
|  |  | VIN / VDD=2.375V, VVDDQSNS=1.8V, VTT=VVTTREF - 50mV (DDR2), $10=2 \mathrm{~A}$ |  | 245 | 400 | mV | 27.x |
|  |  | VIN / VDD=2.375V, VVDDQSNS=1.5V, VTT=VVTTREF - 50mV (DDR3), $\mathrm{IO}=0.5 \mathrm{~A}$ |  | 54 | 230 | mV | 28.x |
|  |  | $\begin{aligned} & \mathrm{VIN} / \mathrm{VDD}=2.375 \mathrm{~V}, \mathrm{VVDDQSNS}=1.5 \mathrm{~V}, \mathrm{VTT}=\mathrm{VVTTREF}-50 \mathrm{mV} \text { (DDR3), } \\ & \mathrm{IO}=1 \mathrm{~A} \end{aligned}$ |  | 109 | 300 | mV | 28.x |
|  |  | VIN / VDD=2.375V, VVDDQSNS=1.5V, VTT=VVTTREF - 50mV (DDR3), $1 \mathrm{O}=2 \mathrm{~A}$ |  | 230 | 400 | mV | 28.x |
|  |  | VIN / VDD=2.375V, VVDDQSNS=1.35V, VTT=VVTTREF - 50 mV (DDR3L), IO=0.5A |  | 53 | 230 | mV | 28.x |
|  |  | VIN / VDD=2.375V, VVDDQSNS=1.35V, VTT=VVTTREF - 50 mV (DDR3L), IO=1A |  | 107 | 300 | mV | 28.x |
|  |  | VIN / VDD=2.375V, VVDDQSNS=1.35V, VTT=VVTTREF - 50 mV (DDR3L), IO=2A |  | 223 | 400 | mV | 28.x |
|  |  | $\begin{aligned} & \text { VIN / VDD=2.375V, VVDDQSNS=1.2V, VTT=VVTTREF - } 50 \mathrm{mV} \text { (DDR4), } \\ & \text { IO }=0.5 \mathrm{~A} \end{aligned}$ |  | 51 | 230 | mV | 29.x |
|  |  | $\begin{aligned} & \mathrm{VIN} / \mathrm{VDD}=2.375 \mathrm{~V}, \mathrm{VVDDQSNS}=1.2 \mathrm{~V}, \mathrm{VTT}=\mathrm{VVTTREF}-50 \mathrm{mV} \text { (DDR4), } \\ & \mathrm{IO}=1 \mathrm{~A} \end{aligned}$ |  | 105 | 300 | mV | 29.x |
|  |  | VIN / VDD=2.375V, VVDDQSNS=1.2V, VTT=VVTTREF - 50mV (DDR4), $1 \mathrm{O}=2 \mathrm{~A}$ |  | 216 | 400 | mV | 29.x |
| V Votolintttol | Output voltage tolerance to $V_{\text {DDQSNS }}$ | $-3 \mathrm{~A}<\mathrm{IVO}<3 \mathrm{~A}$, across Vin voltage range | -35 | +/- 25 | 35 | mV | 20.x, 21.x, 22.x |

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Table 3. TPS7H3301-SP Specifications (continued)

| PARAMETER |  | TEST CONDITION | TPS7H3301-SP |  |  |  | ATE Test \# |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | MIN | TYP | MAX | UNIT |  |
| $\mathrm{V}_{\text {doasns }}$ AND $\mathrm{V}_{\text {VTTREF }}$ OUTPUT |  |  |  |  |  |  |  |
| $\mathrm{V}_{\text {DDOSNS }}$ | Voltage range |  |  | 1 |  | 3.6 | V | Covered in all tests |
| $\mathrm{V}_{\text {TTREF }}$ | $\mathrm{V}_{\text {TTREF }}$ voltage |  |  | VDDQSNS/2 |  | v | 16.x, 17.x |
| $\mathrm{V}_{\text {Vttref }}$ | $\mathrm{V}_{\text {VTTREF }}$ voltage tolerance to $V_{\text {DDQSNS }}$ | -10 mA < IVVTREF < 10 mA , VVDDQSNS $=2.5 \mathrm{~V}$ | -15 |  | 15 | mV | 16.x, 17.x |
|  |  | -10 mA < IVVTREF < 10 mA , VVDDQSNS $=1.8 \mathrm{~V}$ | -15 |  | 15 | mV | 16.x, 17.x |
|  |  | -10 mA < IVVTREF < 10 mA , VVDDQSNS $=1.5 \mathrm{~V}$ | -15 |  | 15 | mV | 16.x, 17.x |
|  |  | -10 mA < IVVTREF < 10 mA , VVDDQSNS $=1.35 \mathrm{~V}$ | -15 |  | 15 | mV | 16.x, 17.x |
|  |  | -10 mA < IVVTREF < 10 mA , VVDDQSNS $=1.2 \mathrm{~V}$ | -15 |  | 15 | mV | 16.x, 17.x |
| UVLO / EN LOGIC THRESHOLD |  |  |  |  |  |  |  |
| $I_{\text {enleak }}$ | Logic input leakage current | EN, $T A=25^{\circ} \mathrm{C}$ | -1 |  | 1 | $\mu \mathrm{A}$ | 2.7 |

## Test Results

This appendix contains the detailed test results.

Delta Threshold $10.00 \%$

NDD Report
THS7H3301-SP
NDD Report
THS7H3301-SP









NDD Report
THS7H3301-SP

|  |  | 16.6_VTTRef_delta_1p35VIdo |  |  |
| :---: | :---: | :---: | :---: | :---: |
|  | Test Site | Junkins | Junkins |  |
|  | Tester | FETS10 | FETS10 |  |
|  | Test Number | EF636800 | EF636800 |  |
|  | Unit | mV | mV |  |
|  | Max Limit | 14 | 15 |  |
|  | Min Limit | -14 | -15 |  |
| n/cm2 | Serial \# | Pre | Post | Delta |
| 0 | 67 | 0.343 | 0.362 | -0.019 |
| 1E+12 | 78 | 0.387 | 0.293 | 0.094 |
| $1 \mathrm{E}+12$ | 81 | 0.306 | 0.330 | -0.024 |
| $1 \mathrm{E}+12$ | 82 | 0.305 | 0.330 | -0.025 |
| 5E+12 | 75 | 0.331 | 0.301 | 0.030 |
| $5 \mathrm{E}+12$ | 79 | 0.378 | 0.286 | 0.092 |
| $5 \mathrm{E}+12$ | 80 | 0.304 | 0.357 | -0.053 |
| 1E+13 | 68 | 0.357 | 0.295 | 0.062 |
| $1 \mathrm{E}+13$ | 71 | 0.329 | 0.313 | 0.016 |
| $1 \mathrm{E}+13$ | 74 | 0.340 | 0.296 | 0.044 |
|  | Max | 0.387 | 0.362 | 0.094 |
|  | Average | 0.338 | 0.316 | 0.022 |
|  | Min | 0.304 | 0.286 | -0.053 |
|  | Std Dev | 0.029 | 0.027 | 0.052 |

















NDD Report
THS7H3301-SP













NDD Report THS7H3301-SP



NDD Report THS7H3301-SP


|  |  | 18.4__VTTRef_noload_1p2VIdo |  |  |
| :---: | :---: | :---: | :---: | :---: |
|  | Test Site | Junkins | Junkins |  |
|  | Tester | FETS10 | FETS10 |  |
|  | Test Number | EF636800 | EF636800 |  |
|  | Unit | V | V |  |
|  | Max Limit | 0.625 | 0.625 |  |
|  | Min Limit | 0.585 | 0.585 |  |
| n/cm2 | Serial \# | Pre | Post | Delta |
| 0 | 67 | 0.606 | 0.606 | -0.001 |
| 1E+12 | 78 | 0.605 | 0.605 | 0.000 |
| 1E+12 | 81 | 0.606 | 0.606 | 0.000 |
| 1E+12 | 82 | 0.606 | 0.606 | 0.000 |
| 5E+12 | 75 | 0.609 | 0.608 | 0.000 |
| 5E+12 | 79 | 0.605 | 0.605 | 0.000 |
| $5 \mathrm{E}+12$ | 80 | 0.609 | 0.609 | 0.000 |
| 1E+13 | 68 | 0.608 | 0.608 | 0.000 |
| 1E+13 | 71 | 0.604 | 0.604 | 0.000 |
| 1E+13 | 74 | 0.609 | 0.608 | 0.000 |
|  | Max | 0.484 | 0.524 | 0.053 |
|  | Average | 0.415 | 0.437 | -0.022 |
|  | Min | 0.384 | 0.391 | -0.140 |
|  | Std Dev | 0.028 | 0.044 | 0.055 |



NDD Report
THS7H3301-SP


## NDD Report <br> THS7H3301-SP






18.33 _VTpadefesfisnklload_2p5I

NDD Report
THS7H3301-SP
Average
Min
Min
0.757
0.754
0.757
0.757
0.000 0.001


NDD Report
THS7H3301-SP

120.000
18.35__VTTRef_LoadRegsnk_2p5VIdo
120.000

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NDD Report
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